

Radiation Hardened Adjustable Positive Voltage Regulator

The Radiation Hardened HS-117RH is an adjustable positive voltage linear regulator capable of operating up to 40VDC. The voltage is adjustable from 1.2V to 37V with two external resistors. The device is capable of sourcing from 50mA to 1.25A_{PEAK} (Min). Protection is provided by the on-chip thermal shutdown and output current limiting circuitry.

The Intersil HS-117RH has advantages over other industry standard types, in that circuitry is incorporated to minimize the effects of radiation and temperature on device stability. Negligible low dose rate sensitivity is achieved through the use of vertical transistor geometries.

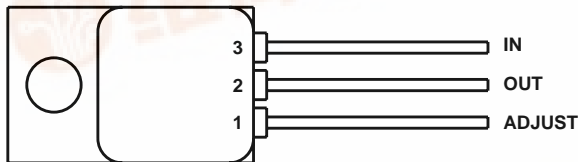
Constructed with the Intersil dielectrically isolated Rad Hard Silicon Gate (RSG) process, the HS-117RH is immune to Single Event Latch-up and has been specifically designed to provide highly reliable performance in harsh radiation environments.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

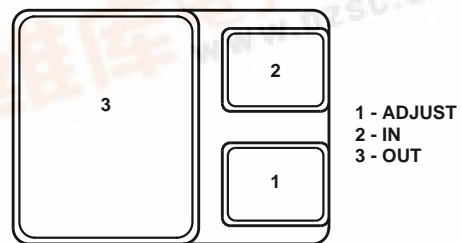
Detailed Electrical Specifications for the HS-117RH are contained in SMD 5962-99547. A "hot-link" is provided on our homepage for downloading.
www.intersil.com/spacedefense/space.asp

Pinout

HS9S-117RH (TO-257AA FLANGE MOUNT)
TOP VIEW



HSYE-117RH (SMD.5 CLCC)
BOTTOM VIEW



Features

- Electrically Screened to DSSC SMD # 5962-99547
- QML Qualified per MIL-PRF-38535 Requirements
- Radiation Environment
 - 300kRAD(Si) (Max)
 - Latch-up Immune
 - Negligible Low Dose Rate Effects Sensitivity
- Superior Temperature Stability
- Over-Temp and Over-Current/Voltage Protection

Applications

- Switch Mode DC - DC Power Conversion
- Housekeeping Supplies for Motors
- Power Supplies for Robotic Control

Ordering Information

ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMP. RANGE (°C)
5962F9954701VXC	HS9S-117RH-Q	-55 to 125
5962F9954701QXC	HS9S-117RH-8	-55 to 125
5962F9954701VYA	HSYE-117RH-Q	-55 to 125
5962F9954701QYA	HSYE-117RH-8	-55 to 125
HS9S-117RH/Proto	HS9S-117RH/Proto	-55 to 125
HSYE-117RH/Proto	HSYE-117RH/Proto	-55 to 125

NOTE: No current JEDEC outline for the SMD.5 package. Refer to SMD for package dimensions. The TO-257 is a totally isolated metal package.



HS-117RH

Die Characteristics

DIE DIMENSIONS

2616 μm x 2794 μm (103 mils x 110 mils)
483 μm \pm 25.4 μm (19 mils \pm 1 mil)

INTERFACE MATERIALS

Glassivation:

Type: Silox (SiO_2)
Thickness: 8.0k \AA \pm 1.0k \AA

Top Metallization:

Type: AlSiCu
Thickness: 16.0k \AA \pm 2k \AA

Substrate:

Radiation Hardened Silicon Gate,
Dielectric Isolation

Backside Finish:

Gold

ASSEMBLY RELATED INFORMATION

Substrate Potential:

Unbiased (DI)

ADDITIONAL INFORMATION

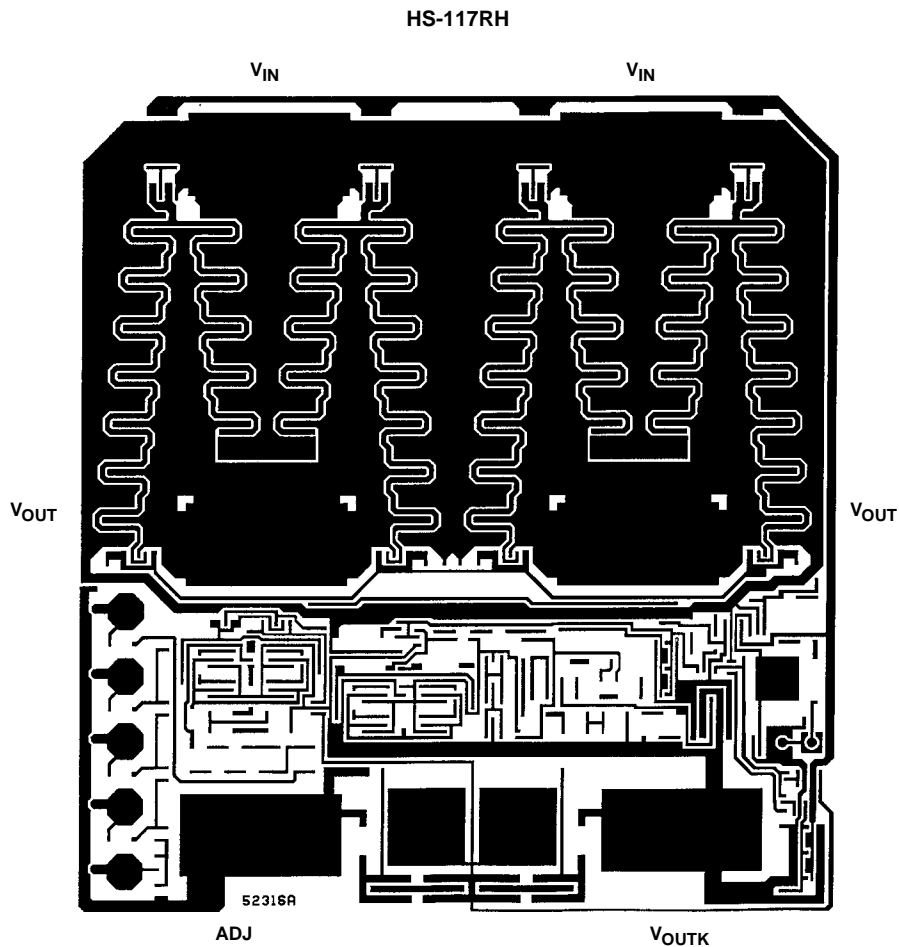
Worst Case Current Density:

$< 2.0 \times 10^5 \text{ A/cm}^2$

Transistor Count:

95

Metallization Mask Layout



All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site www.intersil.com